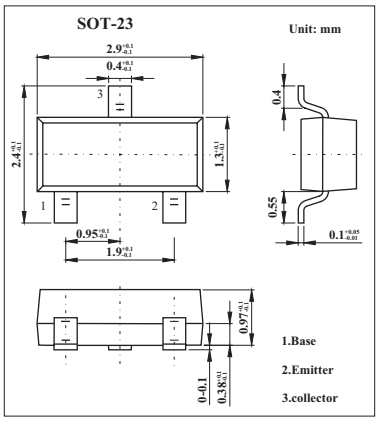
Silicon PNP Epitaxial Planar Type

2SC2404



■ Features

- Optimum for RF amplification of FM/AM radios
- High transition frequency fT
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	15	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = 10 μA, I_E = 0	30			V
Emitter-base voltage	V_{EBO}	I_E = 10 μA, I_C = 0	3			V
Base-emitter voltage	V_{BE}	V_{CB} = 6 V, I_E = -1 mA		0.72		V
Forward current transfer ratio	h_{FE}	V_{CB} = 6 V, I_E = -1 mA	65		260	
Transition frequency	f_T	V_{CB} = 6 V, I_E = -1 mA, f = 100 MHz	450	650		MHz
Reverse transfer capacitance	C_{re}	V_{CB}= 6 V, I_E = -1 mA, f = 10.7 MHz		0.8	1.0	pF
Power gain	G_P	V_{CB}= 6 V, I_E = -1 mA, f = 100 MHz		24		dB
Noise figure	NF	V_{CB}= 6 V, I_E = -1 mA, f = 100 MHz		3.3		dB

■ h_{FE} Classification

Marking	U	
Rank	C	D
h_{FE}	65～160	100～260